84D 27422



PN/MPS/FTSO3638

PNP Small Signal General Purpose Amplifiers & Switches

• VCEO ... -25 V (Min)

h_{FE} ... 30 (Min) (PN/MPS/FTSO3638), 100 (Min) (PN/MPS/FTSO3638A) @ 50 mA

t_{on} ... 75 ns (Max) @ 300 mA; t_{off} ... 170 ns (Max) @ 300 mA

Complements ... PN3641, PN3643

PACKAGE

PN3638 PN3638A TO-92 TO-92

MPS3638 MPS3638A TO-92 TO-92

FTSO3638 FTSO3638A

TO-236AA/AB TO-236AA/AB

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature
Operating Junction Temperature

-55° C to 150° C

150° C

Power Dissipation (Notes 2 & 3)

Total Dissipation at PN/MPS F 25° C Ambient Temperature 0.625 W 0.35° C Case Temperature 1.0 W

Voltages & Currents
VCEO Collector to Emitter Voltage (Note 4)
VCBO Collector to Base Voltage

V_{CES} Collector to Emitter Voltage V_{EBO} Emitter to Base Voltage I_C Collector Current (Note 2) FTSO

0.350 W*

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

-25 V

-25 V

-25 V

-4.0 V

500 mA

		36	38	3638A			
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	UNITS	TEST CONDITIONS
BV _{CES}	Collector to Emitter Breakdown Voltage	-25		-25		V	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$
ВVсво	Collector to Base Breakdown Voltage	-25		-25		٧	$I_C = 100 \ \mu A, \ V_{BE} = 0$
BV _{EBO}	Emitter to Base Breakdown Voltage	[4.0		-4.0		V	$I_E = 100 \ \mu A, \ I_C = 0$
Ices	Collector Reverse Current		35 2.0		35 2.0	nΑ μΑ	$V_{CE} = -15 \text{ V}, V_{BE} = 0$ $V_{CE} = -15 \text{ V}, V_{BE} = 0,$ $T_A = 65^{\circ} \text{ C}$

NOTES:

- 1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
- 2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8 0 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
- 4. Rating refers to a high current point where collector to emitter voltage is lowest.
- 5. Pulse conditions: length = 300 µs; duty cycle = 1%.
- 6. For product family characteristic curves, refer to Curve Set T212.
- * Package mounted on 99,5% alumina 8 mm x 8 mm x 0.6 mm.

3469674 0027423 5 84D 27423 D

3469674 FAIRCHILD SEMICONDUCTOR

PN/MPS/FTSO3638 PN/MPS/FTSO3638A

T-37-15

014501	OLIA DA OTERIOTIO		38		38A	LIMITO	TEST CONDITIONS
SYMBOL	CHARACTERISTIC DC Pulse Current Gain (Note 5)	MIN	MAX	MIN	MAX_	UNITS	TEST CONDITIONS
h _{FE}	(MPS3638)	20 30 20		100 80 100 20			$\begin{array}{l} I_{C} = 10 \text{ mA}, \ V_{CE} = -10 \text{ V} \\ I_{C} = 10 \text{ mA}, \ V_{CE} = -10 \text{ V} \\ I_{C} = 1.0 \text{ mA}, \ V_{CE} = -10 \text{ V} \\ I_{C} = 50 \text{ mA}, \ V_{CE} = -1.0 \text{ V} \\ I_{C} = 300 \text{ mA}, \ V_{CE} = -2.0 \text{ V} \end{array}$
VCEO(sus)	Collector to Emitter Sustaining Voltage (Notes 4 & 5)	-25		-25		٧	$I_C = 10 \text{ mA}, I_B = 0$
VCE(sat)	Collector to Emitter Saturation Voltage (Pulsed) (Note 5)		-0.25 -1.0		-0.25 -1.0	>>	$I_C = 50$ mA, $I_B = 2.5$ mA1 $I_C = 300$ mA, $I_B = 30$ mA
V _{BE(sat)}	Base to Emitter Saturation Voltage (Note 5)	-0.8	-1.1 -2.0	-0.8	−1.1 −2.0	>>	$I_{C} = 50$ mA, $I_{B} = 2.5$ mA $I_{C} = 300$ mA, $I_{B} = 30$ mA
Сов	Common Base Open Circuit, Output Capacitance		20		10	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 140 \text{ kHz}$
Сіь	Common Base Open Circuit, Input Capacitance (PN3638A) (MPS3638A)		65		35 25	pF pF	$V_{EB} = -0.5 \text{ V}, I_C = 0, f = 140 \text{ kHz}$ $V_{EB} = -0.5 \text{ V}, I_C = 0, f = 140 \text{ kHz}$
h _{fe}	Magnitude of Small Signal Current Gain	1.0		1.5			$I_{C} = 50$ mA, $V_{CE} = -3.0$ V, $f = 100$ MHz
h _{fe}	Small Signal Current Gain (PN3638) (MPS3638)	25 25	180	100			$I_C = 10$ mA, $V_{CE} = -10$ V, f = 1.0 kHz $I_C = 10$ mA, $V_{CE} = -10$ V, f = 1.0 kHz $I_C = 10$ mA, $V_{CE} = -10$ V, f = 1.0 kHz
h _{ře}	Input Resistance (MPS3638)		2000 1500		2000	Ω	$I_{C} = 10$ mA, $V_{CE} = 10$ V, $f = 1.0$ kHz
hoe	Output Conductance		1200		1200	μmhos	$I_{C} = 10 \text{ mA}, V_{CE} = -10 \text{ V},$ f = 1.0 kHz
h _{re}	Voltage Feedback Ratio		2600		1500	x10-6	$I_C = 10 \text{ mA}, V_{CE} = -10 \text{ V},$ f = 1.0 kHz
ton	Turn On Time (test circuit no. 536)		75		75	ns	$I_{C} \approx 300$ mA, $I_{B1} \approx 30$ mA, $V_{CC} = 10$ V
toff	Turn Off Time (test circuit no. 536)		170		170	ns	$I_C \approx 300 \text{ mA}, I_{B1} \approx I_{B2} \approx 30 \text{ mA}$ $V_{CC} = 10 \text{ V}$

84D 27424

D 🕳

PN/MPS/FTSO3639 PN/MPS/FTSO3640

PNP High Speed Saturated Logic Switches T-37-15

V_{CEO} ... 12 V (Min) (PN/MPS3640)

ton ... 25 ns (Max) @ 50 mA, 60 ns (Max) @ 10 mA;
 toff ... 35 ns (Max) @ 50 mA, 75 ns (Max) @ 10 mA

Complements ... PN4274, 2N5769

PACKAGE

PN3639 TO-92 PN3640 TO-92 MPS3639 TO-92 MPS3640 TO-92 FTSO3639 TO-336AA/

FTSO3639 FTSO3640 TO-236AA/AB TO-236AA/AB

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature -55° C to 150° C Operating Junction Temperature 150° C

Power Dissipation (Notes 2 & 3)

Total 25° C	Dissipation at Ambient Temperature Case Temperature	PN/MPS 0.625 W 1.0 W	FTSO 0.350 W*
	ges & Currents Collector to Emitter Voltage	3639 6 ∨	3640 −12 V
ACEO	(Note 4)	0 1	12 4
V_{CBO}	Collector to Base Voltage	−6 V	−12 V
V_{EBO}	Emitter to Base Voltage	-4.0 V	-4.0 V
lc	Collector Current	80 mA	80 mA

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

			3639		3640		
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	UNITS	TEST CONDITIONS
BV _{CES}	Collector to Emitter Breakdown Voltage	-6.0		-12.0		V	$I_C = 100 \ \mu A$, $V_{BE} = 0$
ВVсво	Collector to Base Breakdown Voltage	-6.0		-12.0		٧	$I_{C} = 100 \ \mu\text{A}, \ I_{E} = 0$
BV _{EBO}	Emitter to Base Breakdown Voltage	-4.0		-4.0		٧	$I_E = 100 \ \mu A, \ I_C = 0$
ICES	Collector Reverse Current		50 1.0		50 1.0	nΑ nΑ μΑ	$\begin{array}{l} V_{CE} = -3.0 \text{ V, } V_{BE} = 0 \\ V_{CE} = -6.0 \text{ V, } V_{BE} = 0 \\ V_{CE} = -3.0 \text{ V, } V_{BE} = 0, T_A = 65^{\circ}\text{ C} \\ V_{CE} = -6.0 \text{ V, } V_{BE} = 0, T_A = 65^{\circ}\text{ C} \end{array}$
h _{FE}	DC Pulse Current Gain (Note 5)	30 20	120	30 20	120		$I_C = 10 \text{ mA}, V_{CE} = -0.3 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = -1.0 \text{ V}$

NOTES:

- 1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
- 2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- These ratings give a maximum junction temperature of 150°C and (TO-92) junction-to-case thermal resistance of 125°C/W (derating factor of 8.0 mW/°C); junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 357°C/W (derating factor of 2.8 mW/°C).
- 4. Rating refers to a high current point where collector to emitter voltage is lowest.
- 5. Pulse conditions: length = 300 µs; duty cycle = 1%.
- 6. For product family characteristic curves, refer to Curve Set T292.
- * Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

. 84D 27425

D ____

PN/MPS/FTSO3639 PN/MPS/FTSO3640

		PN:	3639	PN	3640		
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	UNITS	TEST CONDITIONS
V _{CEO(sus)}	Collector to Emitter Sustaining Voltage (Note 5)	-6.0		-12		٧	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$
V _{CE(sat)}	Collector to Emitter Saturation Voltage (Note 4)		-0.16 -0.5 -0.25 -0.23		-0.2 -0.6 0.3 0.25	>>>>	$\begin{array}{l} I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA, } I_{B} = 5.0 \text{ mA} \\ I_{C} = 10 \text{ mA, } I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA,} \\ T_{A} = 65^{\circ} \text{ C} \end{array}$
VBE(sat)	Base to Emitter Saturation Voltage (Note 5)	-0.75 -0.8	-0.95 -1.0 1.5	-0.75 -0.8	-0.95 -1.0 1.5	<<<	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$
Сов	Output Capacitance		3.5 5.5		3.5 5.5	pF pF	$V_{CB} = -5.0 \text{ V}, I_E = 0, f = 140 \text{ kHz}$ $V_{CB} = 0, I_E = 0, f = 140 \text{ kHz}$
Cib	Input Capacitance		3.5		3.5	pF	$V_{EB} = -0.5 \text{ V}, I_C = 0, f = 140 \text{ kHz}$
h _{fe}	High Frequency Current Gain	3.0 5.0		3.0 5.0			$\begin{array}{l} I_{C} = 10 \text{ mA, V}_{CB} = 0, \\ f = 100 \text{ MHz} \\ I_{C} = 10 \text{ mA, V}_{CE} = -5.0 \text{ V,} \\ f = 100 \text{ MHz} \end{array}$
$ au_{\mathrm{g}}$	Storage Time (test circuit no. 234)		30		50	ns	$I_{C} \simeq 10$ mA, $I_{B1} \simeq I_{B2} \simeq 10$ mA, $V_{CC} = 3.0$ V
tan	Turn On Time (test circuit no. 235) (test circuit no. 219)		25 60		25 60	ns ns	$\begin{array}{l} I_C \simeq 50 \text{ mA, } I_{B1} \simeq 5.0 \text{ mA,} \\ V_{CC} = 6.0 \text{ V} \\ I_C \simeq 10 \text{ mA, } I_{B1} \simeq 0.5 \text{ mA,} \\ V_{CC} = -1.5 \text{ V} \end{array}$
t _{off}	Turn Off Time (test circuit no. 235) (test circuit no. 219)		25 60		35 75	ns ns	$\begin{array}{l} I_{C}\simeq50~\text{mA},~I_{\text{B1}}\simeq I_{\text{B2}}\simeq5.0~\text{mA},\\ V_{\text{CC}}=6.0~\text{V}\\ I_{C}\simeq10~\text{mA},~I_{\text{B1}}\simeq I_{\text{B2}}\simeq0.5~\text{mA},\\ V_{\text{CC}}=1.5~\text{V} \end{array}$

SYMBOL	CHARACTERISTIC	MPS MIN	3639 MAX	MPS MIN	3640 MAX	UNITS	TEST CONDITIONS
BV _{CES}	Collector to Emitter Breakdown Voltage	-6.0		-12.0		V	$I_C = 100 \ \mu A, \ V_{BE} = 0$
ВVсво	Collector to Base Breakdown Voltage	-6.0		-12.0		٧	$I_C = 100 \ \mu A, \ I_E = 0$
BV _{EBO}	Emitter to Base Breakdown Voltage	-4.0		-4.0		V	$I_E = 100 \ \mu A, \ I_C = 0$
ICES	Collector Reverse Current		10		10	nA nA μA μA	$V_{CE} = -3.0 \text{ V}, V_{BE} = 0$ $V_{CE} = -6.0 \text{ V}, V_{BE} = 0$ $V_{CE} = -3.0 \text{ V}, V_{BE} = 0, T_A = 65^{\circ} \text{ (}$ $V_{CE} = -6.0 \text{ V}, V_{BE} = 0, T_A = 65^{\circ} \text{ (}$



PN/MPS/FTSO3639 PN/MPS/FTSO3640 7.37-15

SYMBOL	CHARACTERISTIC	MPS MIN	3639 MAX	MPS MIN	3640 MAX	UNITS	TEST CONDITIONS
h _{FE}	DC Pulse Current Gain (Note 5)	30 20	120	30 20	120		$I_{C} = 10$ mA, $V_{CE} = -0.3$ V $I_{C} = 50$ mA, $V_{CE} = -1.0$ V
V _{CEO(sus)}	Collector to Emitter Sustaining Voltage (Note 5)	-6.0		-12		V	$I_{C} = 10 \text{ mA}, I_{B} = 0$
V _{CE(sat)}	Collector to Emitter Saturation Voltage (Note 5)		-0.16 -0.5 -0.23		-0.2 -0.6 -0.25	V V V	$\begin{array}{l} I_{C} = 10 \text{ mA}, \ I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, \ I_{B} = 5.0 \text{ mA} \\ I_{C} = 10 \text{ mA}, \ I_{B} = 1.0 \text{ mA}, \\ T_{A} = 65^{\circ} \text{ C} \end{array}$
V _{BE(sat)}	Base to Emitter Saturation Voltage (Note 5)	0.75 0.8	-0.95 -1.0 1.5	-0.75 -0.8	-0.95 -1.0 1.5	V V V	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
Соь	Output Capacitance		3.5		3.5	pF	$V_{CB} = -5.0 \text{ V}, I_E = 0, f = 140 \text{ k}$
Cib	Input Capacitance		3.5		3.5	pF	$V_{EB} = -0.5 \text{ V}, I_C = 0, f = 140 \text{ k}$
h _{fe}	High Frequency Current Gain	3.0 5.0		5.0			$ \begin{aligned} I_C &= 10 \text{ mA, } V_{CB} = 0, \\ f &= 100 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = -5.0, \\ f &= 100 \text{ MHz} \end{aligned} $
ton	Turn On Time (test circuit no. 235) (test circuit no. 219)		25 60		25 60	ns ns	$\begin{array}{c} I_{C} \simeq 50 \text{ mA, } I_{B1} \simeq 5.0 \text{ mA,} \\ V_{CC} = 6.0 \text{ V} \\ I_{C} \simeq 10 \text{ mA, } I_{B1} \simeq 0.5 \text{ mA,} \\ V_{CC} = -1.5 \text{ V} \end{array}$
t _{off}	Turn Off Time (test circuit no. 235) (test circuit no. 219)		25 60		35 75	ns ns	$I_{C} \simeq 50$ mA, $I_{B1} \simeq I_{B2} \simeq 5.0$ m $V_{CC} = -6.0$ V $I_{C} \simeq 10$ mA, $I_{B1} \simeq I_{B2} \simeq 0.5$ m $I_{CC} \simeq 1.5$ V

84D 27427



PN3641/FTSO3641 T- 29-23 PN3642/FTSO3642 PN3643/FTSO3643 NPN General Purpose Small Signal **Amplifiers**

_	V _{CEO} 30 V (Min) (PN/FTSO3641, PN/FTSO3643),	PACKAGE	
Ø	ACEO 30 A (MIII) (LIALI LOGOCHI)	PN3641	TO-92
	45 V (Min) (PN/FTSO3642)	PN3642	TO-92
0	h _{FE} 100 (Min) @ 150 mA, 25 (Min) @ 500 mA	PN3643	TO-92
	(PN/FTSO3643)	FTSO3641	TO-236AA/AB
0	Pg 400 mW RF Power Out at 30 MHz	FTSO3642	TO-236AA/AB
0	f _T 250 MHz (Min) (PN3643)	FTSO3643	TO-236AA/AB
6	ton 60 ns (Max) @ 300 mA, toff 150 ns (Max) @ 300 mA	F1503043	10-20017/70

ABSOLUTE MAXIMUM RATINGS (Note 1)

Complements ... MPS3638/A, PN3644

Temperatures

-55° C to 150° C Storage Temperature 150° C Operating Junction Temperature

Power Dissipation (Notes 2 & 3)

Total Dissipation at 25° C Ambient Temperature 25° C Case Temperature	PN 0.625 W 1.0 W	FTSO 0.350 W*
Voltages & Currents VCEO Collector to Emitter Voltage (Note 4)	3641/3 30 V	3642 45 V
V _{CBO} Collector to Base Voltage V _{EBO} Emitter to Base Voltage I _C Collector Current	60 V 5.0 V 500 mA	60 V 5.0 V 500 mA

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

		3641		3642			
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	UNITS	TEST CONDITIONS
BV _{CEO(sus)}	Collector to Emitter Breakdown Voltage (Notes 4 & 5)	30		45		٧	$I_{C} = 10 \text{ mA}, I_{B} = 0$
BV _{CES}	Collector to Emitter Breakdown Voltage	60		60		V	$I_{C} = 10 \ \mu A, \ V_{BE} = 0$
ВУсво	Collector to Base Breakdown Voltage	60		60		V	$I_{C} = 10 \ \mu A, \ I_{E} = 0$
BV _{EBO}	Emitter to Base Breakdown Voltage	5.0		5.0		V	$I_E = 10 \ \mu A, I_C = 0$

NOTES:

These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.

These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); 357° C/W (derating factor of 2.8 mW/° C).

Rating refers to a high current point where collector to emitter voltage is lowest. Pulse conditions: length = 300 \(\mu\)s; duty cycle = 1%.

For product family characteristic curves, refer to Curve Set T145.

Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.



84D 27428

D

PN3641/FTSO3641 PN3642/FTSO3642 PN3643/FTSO3643

T-29.23

0)/14001	CHARACTERISTIC	36 MIN	41 MAX	36 MIN	642 MAX	UNITS	TEST CONDITIONS
SYMBOL	Collector Cutoff Current (Note 5)	IVIIIV	50 1.0	Will	50 1.0	nA μA	V _{CE} = 50 V, V _{BE} = 0 V _{CE} = 50 V, V _{BE} = 0, T _A = 65° C
h _{FE}	DC Pulse Current Gain (Note 5)	40 15	120	40 15	120		$I_C = 150$ mA, $V_{CE} = 10$ V $I_C = 500$ mA, $V_{CE} = 10$ V
VCE(sat)	Collector to Emitter Saturation Voltage (Note 5)		0.22		0.22	٧	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$
Сор	Output Capacitance		8.0		8.0	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 140 \text{ kHz}$
h _{fe}	Magnitude of Common Emitter, Short Circuit Small Signal Current Gain	1.5		1.5			$I_{C} = 50 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 100 MHz
GPE	Amplifier Power Gain (test circuit no. 238)	10		10		dB	(Zero Signal) $V_{CE}=15$ V, $I_C=0$, $R_G=140$ Ω , $R_L=260$ Ω , $f=30$ MHz, $P_{IN}=40$ mW
η	Collector Efficiency (test circuit no. 238)	60		60		%	(Zero Signal) $V_{\text{CE}}=15$ V, $I_{\text{C}}=0$, $R_{\text{G}}=140$ Ω , $R_{\text{L}}=260$ Ω , $f=30$ MHz, $P_{\text{IN}}=40$ mW
ton	Turn On Time (test circuit no. 241)		60		60	ns	$I_C \approx 300$ mA, $I_{B1} \approx 30$ mA,
t _{off}	Turn Off Time (test circuit no. 242)		150		150	ns	$I_{\rm C} \approx 300 \text{ mA}, I_{\rm B1} \approx I_{\rm B2} = 30 \text{ mA}$

SYMBOL	CHARACTERISTIC	36 MIN	MAX	UNITS	TEST CONDITIONS
BV _{CEO(sus)}	Collector to Emitter Breakdown Voltage (Notes 4 & 5)	30		٧	$I_{C} = 10 \text{ mA}, I_{B} = 0$
BV _{CES}	Collector to Emitter Breakdown Voltage	60		V	$I_{C} = 10 \ \mu A, \ V_{BE} = 0$
ВVсво	Collector to Base Breakdown Voltage	60		V	$I_{C} = 10 \ \mu A, \ I_{E} = 0$
BV _{EBO}	Emitter to Base Breakdown Voltage	5.0		V	$l_E = 10 \ \mu A, \ l_C = 0$
ICES	Collector Cutoff Current (Note 5)		50 1.0	nA μA	$V_{CE} = 50 \text{ V}, V_{BE} = 0$ $V_{CE} = 50 \text{ V}, V_{BE} = 0,$ $T_A = 65^{\circ} \text{ C}$
h _{FE}	DC Pulse Current Gain (Note 5)	100 25	300		$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$
VCE(sat)	Collector to Emitter Saturation Voltage (Note 5)		0.22	V	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$

84D 27429

D

PN3641/FTSO3641 PN3642/FTSO3642 PN3643/FTSO3643

T-29.23

SYMBOL	CHARACTERISTIC	36 MIN	343 MAX	UNITS	TEST CONDITIONS
Соь	Output Capacitance		8.0	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 140 \text{ kHz}$
h _{fe}	Magnitude of Common Emitter, Short Circuit Small Signal Current Gain	2.5			$I_C = 50$ mA, $V_{CE} = 5.0$ V, $f = 100$ MHz
GPE	'Amplifier Power Gain (test circuit no. 238)	10		dB	(Zero Signal) $V_{CE} = 15 \text{ V}$, $I_C = 0$, $R_G = 140 \Omega$, $R_L = 260 \Omega$, $f = 30 \text{ MHz}$, $P_{IN} = 40 \text{ mW}$
η	Collector Efficiency (test circuit no. 238)	60		%	(Zero Signal) $V_{CE} = 15 \text{ V}$, $I_C = 0$, $R_G = 140 \Omega$, $R_L = 260 \Omega$, $f = 30 \text{ MHz}$, $P_{IN} = 40 \text{ mW}$
t _{on}	Turn On Time (test circuit no. 241)		60	ns	$I_C \approx 300$ mA, $I_{B1} \approx 30$ mA,
toff	Turn Off Time (test circuit no. 242)		150	ns	$I_{\rm C} \approx 300$ mA, $I_{\rm B1} \approx I_{\rm B2} = 30$ mA

